**CNSE NanoFab Tool Calibration Form**

**DATE: \_\_2/18/2016\_\_\_\_\_\_\_\_\_\_\_\_\_\_\_\_**

**Tool Description: \_\_\_\_Unaxis 790 PECVD\_\_**

**Test: SiO2 deposition rate**

**Run Parameters:**

**Sample size: 4” silicon wafer**

**Oxide Recipe: Standard**

**Deposition Time: 10 min**

**Deposition Temp: 250 C**

**Process Gases: SiH4, N2O**

**Average Thickness (9Pts), 10 mm edge exclusion: 5669 A**

**Range: 183 A**

**Standard Deviation: 59**

**Uniformity: 1.6%**

**Deposition rate: 567 A / min**

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**Engineer: CNSE Staff\_Frank Lee\_\_\_\_\_\_\_\_\_\_\_\_\_\_\_\_\_**